

# Xiuyan Li

## List of Publications by Year in descending order

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11  
papers

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1937685  
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docs citations

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times ranked

159  
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis of Using Negative Capacitance FETs to Optimize Linearity Performance for Voltage Reference Generators. IEEE Transactions on Electron Devices, 2021, 68, 5864-5871.	3.0	3
2	The electronics transport mechanism of grain and grain boundary in semiconductive hafnium oxynitride thin film. Journal of Materials Science, 2020, 55, 2881-2890.	3.7	2
3	On the physical origins of time-dependent steep SS in FeFET. , 2020, , .		1
4	Stepwise internal potential jumps caused by multiple-domain polarization flips in metal/ferroelectric/metal/paraelectric/metal stack. Nature Communications, 2020, 11, 1895.	12.8	14
5	Flexible bioelectrodes with enhanced wrinkle microstructures for reliable electrochemical modification and neuromodulation in vivo. Biosensors and Bioelectronics, 2019, 135, 181-191.	10.1	37
6	Interface reaction kinetics in SiGe oxidation. Applied Physics Letters, 2019, 115, .	3.3	6
7	Direct relationship between sub-60 mV/dec subthreshold swing and internal potential instability in MOSFET externally connected to ferroelectric capacitor. , 2018, , .		9
8	Effect of nitrogen passivation on interface composition and physical stress in SiO <sub>2</sub> /SiC(4H) structures. Applied Physics Letters, 2018, 113, .	3.3	12
9	Self-decomposition of SiO <sub>2</sub> due to Si-chemical potential increase in SiO <sub>2</sub> between HfO <sub>2</sub> and substrate - Comprehensive understanding of SiO <sub>2</sub> -IL scavenging in HfO <sub>2</sub> gate stacks on Si, SiGe and SiC. , 2015, , .		0
10	Kinetic model for scavenging of SiO <sub>2</sub> interface layer in HfO <sub>2</sub> gate stacks. , 2014, , .		1
11	Analytical Formulation of SiO <sub>2</sub> -IL scavenging in HfO <sub>2</sub> /SiO <sub>2</sub> /Si gate stacks - A key is the SiO <sub>2</sub> /Si interface reaction. , 2014, , .		2